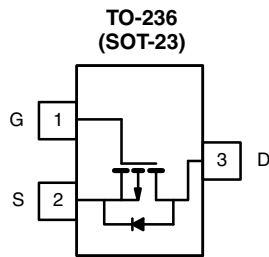


## P-Channel 20 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
-20	0.039 at V <sub>GS</sub> = -4.5 V	-6 <sup>e</sup>	9 nC
	0.050 at V <sub>GS</sub> = -2.5 V	-5.8	
	0.063 at V <sub>GS</sub> = -1.8 V	-5.1	



Top View  
Si2323CDS (P3)\*  
\* Marking Code

**Ordering Information:**  
Si2323CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Load Switch
- PA Switch
- DC/DC Converters

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	-6 <sup>e</sup>
		T <sub>C</sub> = 70 °C	-5.2
		T <sub>A</sub> = 25 °C	-4.6 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	-3.7 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	-20	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	-1 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	2.5
		T <sub>C</sub> = 70 °C	1.6
		T <sub>A</sub> = 25 °C	1.25 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.8 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	≤ 5 s	R <sub>thJA</sub>	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	40	50	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 166 °C/W.
- Package limited.

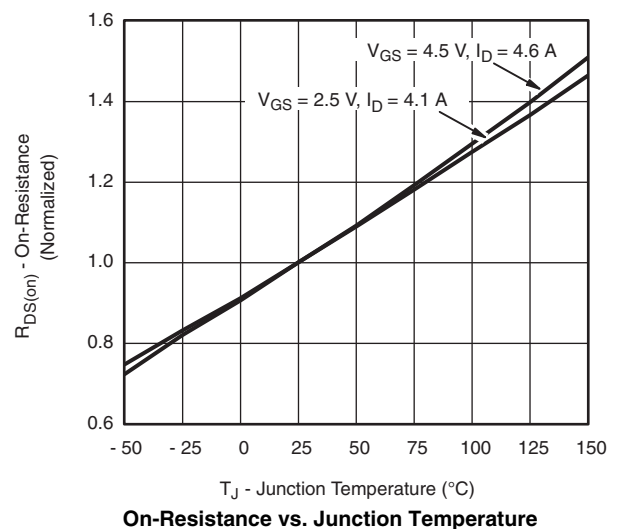
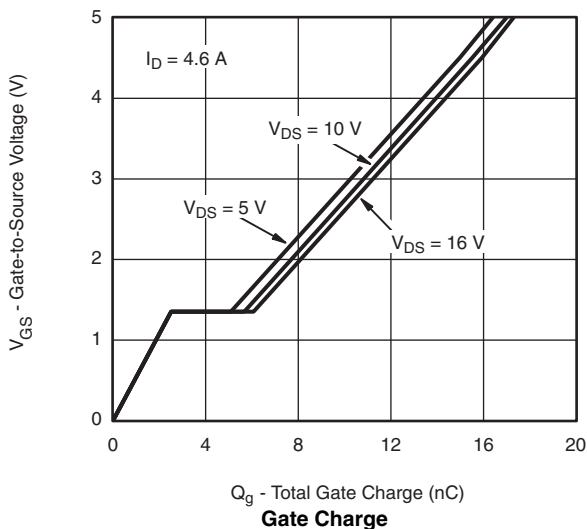
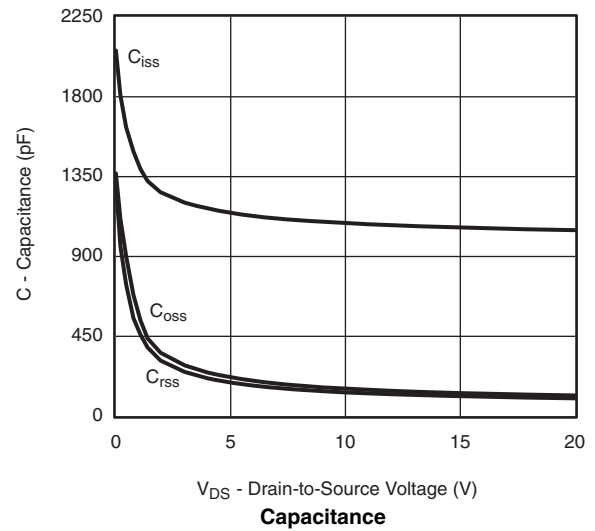
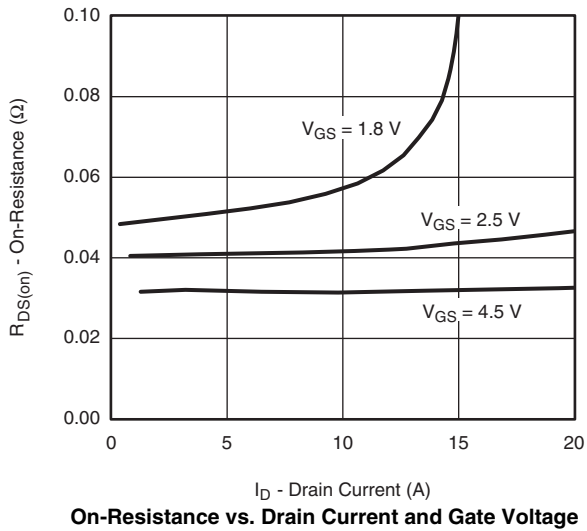
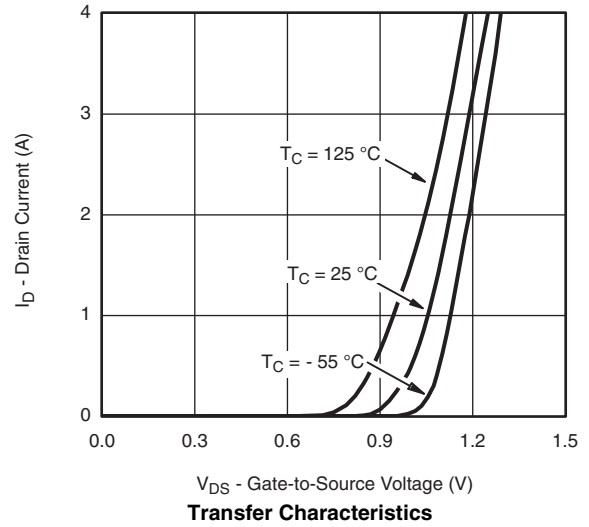
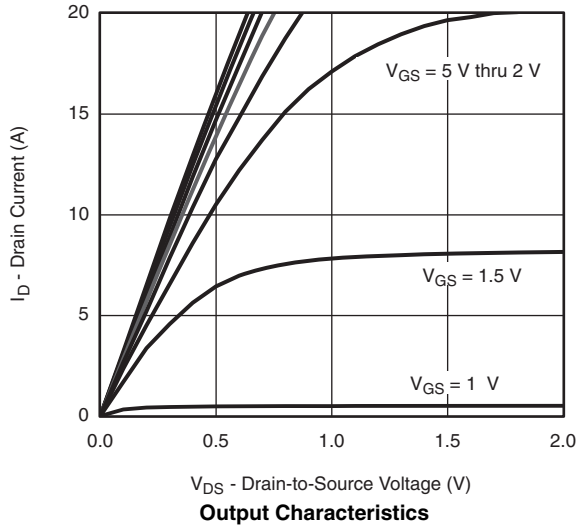
MOSFET SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-14		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}$		0.032	0.039	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -4.1\text{ A}$		0.041	0.050	
		$V_{GS} = -1.8\text{ V}, I_D = -3.6\text{ A}$		0.050	0.063	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -4.6\text{ A}$		20		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1090		pF
Output Capacitance	$C_{oss}$			155		
Reverse Transfer Capacitance	$C_{rss}$			135		
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4.6\text{ A}$		16	25	nC
				9.3	15	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10\text{ V}, V_{GS} = -2.5\text{ V}, I_D = -4.6\text{ A}$		2.5		
Gate-Drain Charge	$Q_{gd}$			3.2		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.8	4.1	8.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 2.7\text{ }\Omega$ $I_D = -3.7\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		15	23	ns
Rise Time	$t_r$			23	35	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	$t_f$			12	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-2.1	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-20	
Body Diode Voltage	$V_{SD}$	$I_S = -3.7\text{ A}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -3.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		30	45	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			20	40	nC
Reverse Recovery Fall Time	$t_a$			17		ns
Reverse Recovery Rise Time	$t_b$			13		

Notes:

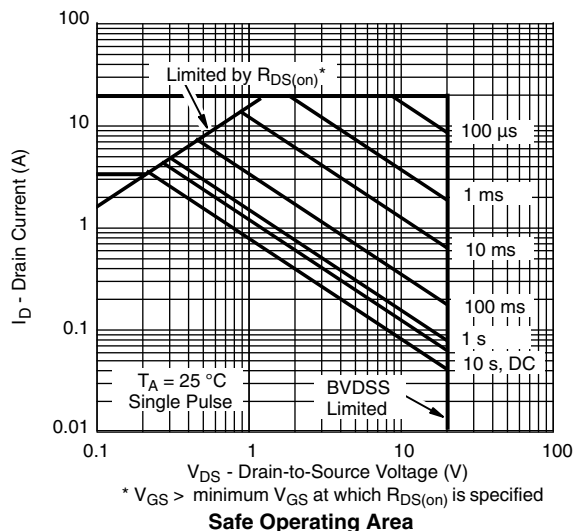
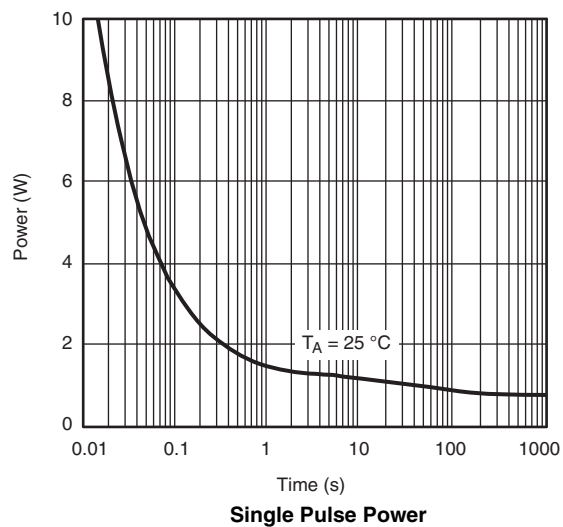
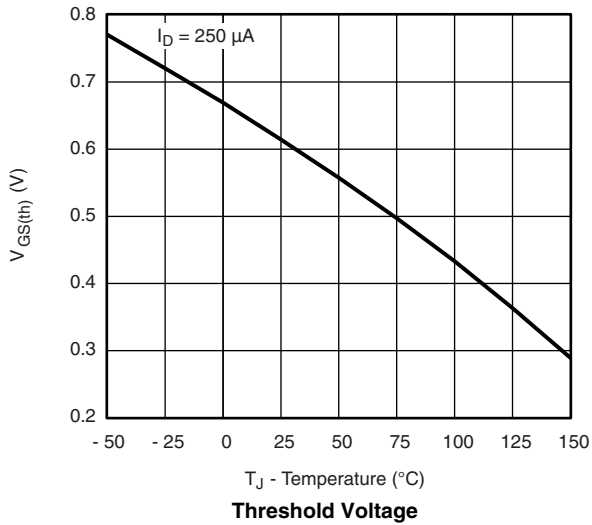
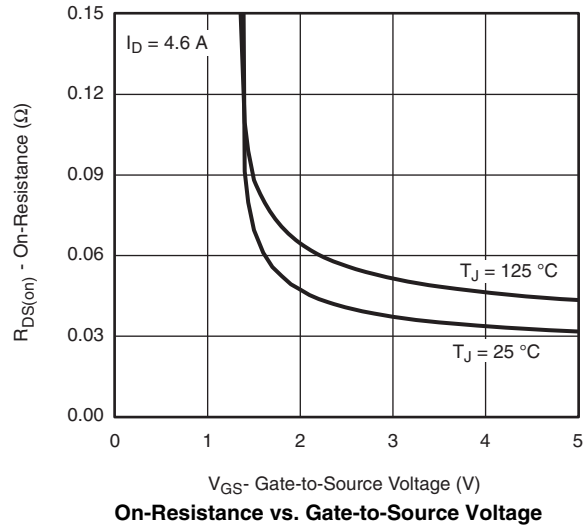
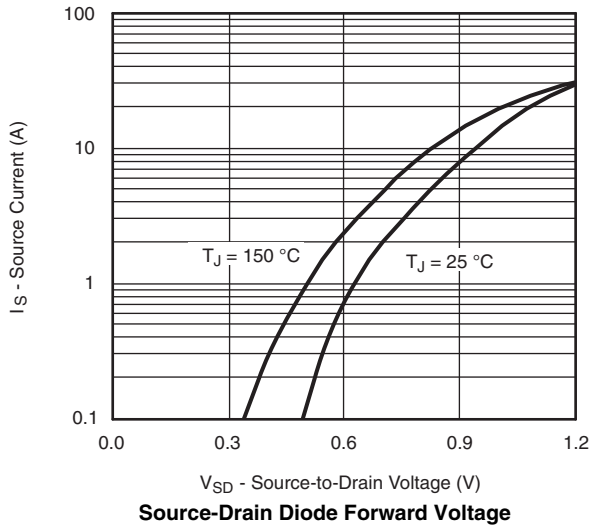
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

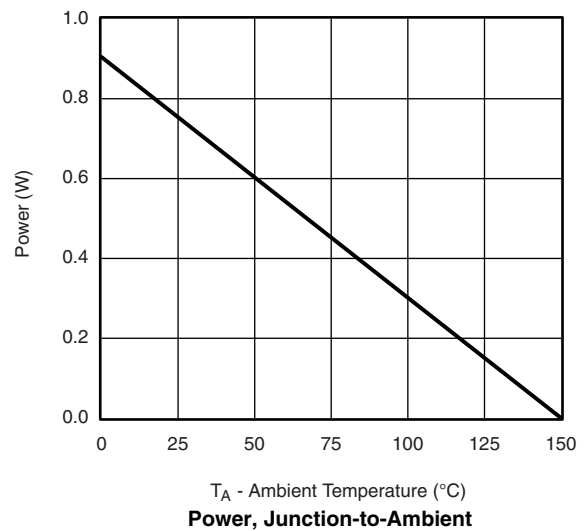
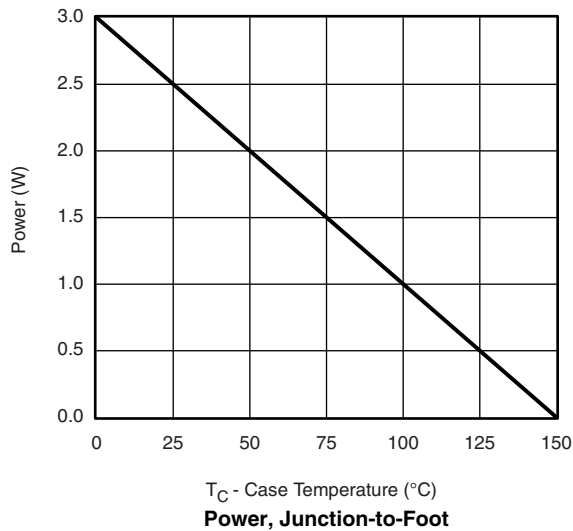
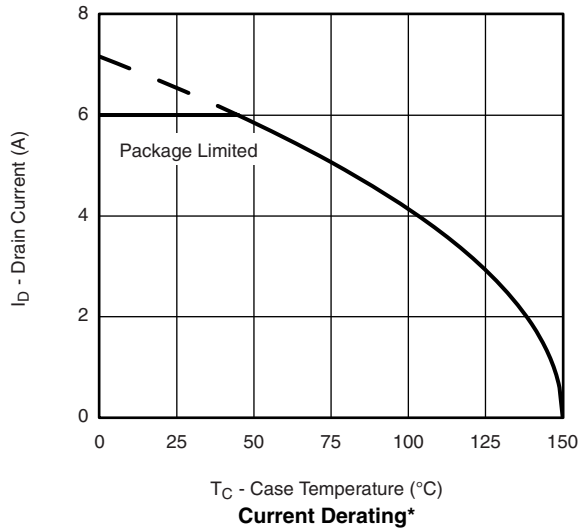
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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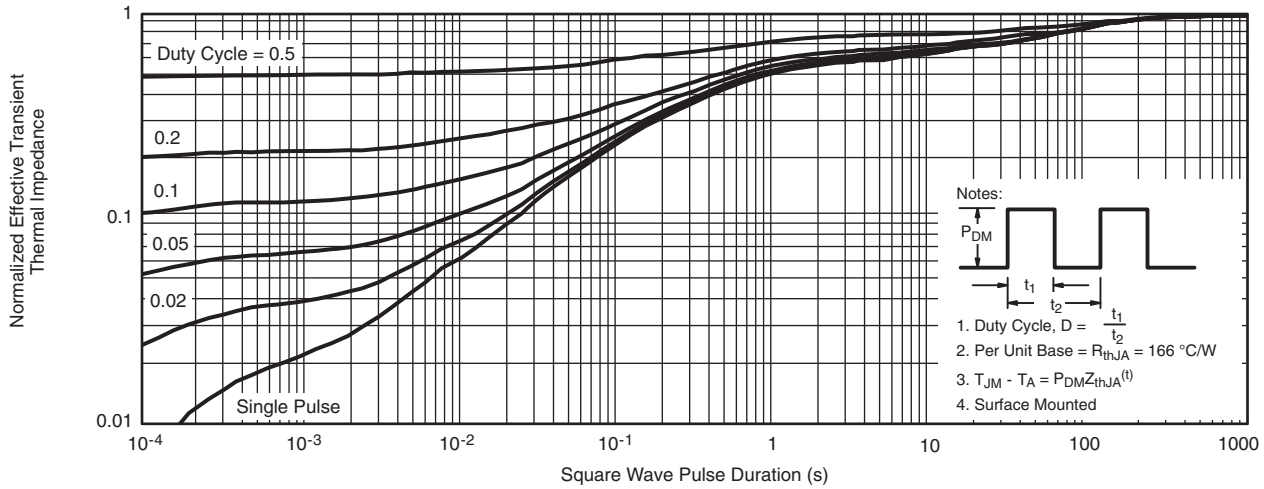


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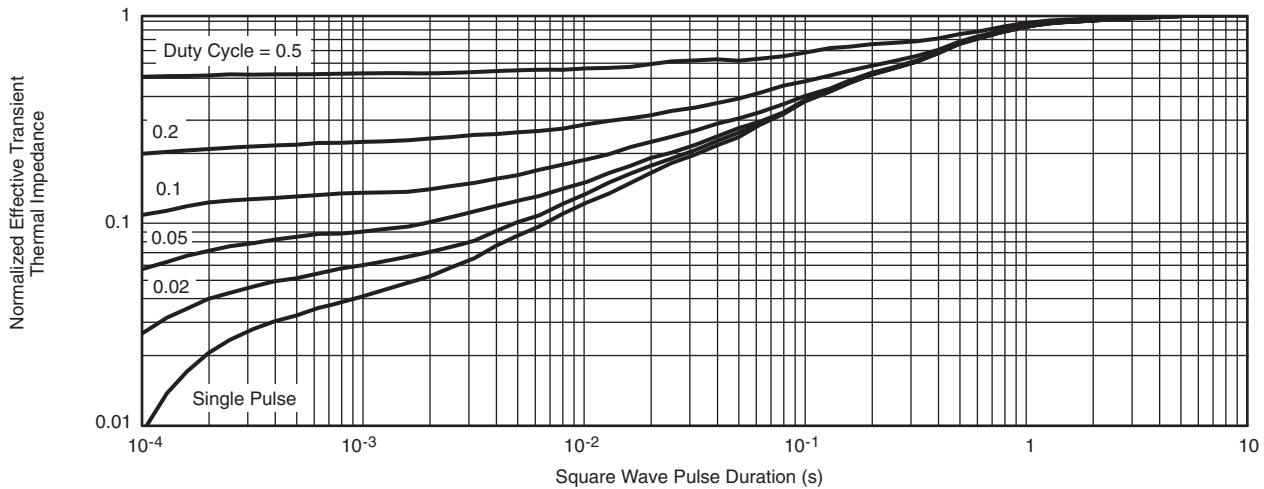


\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?65700](http://www.vishay.com/ppg?65700).

## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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